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Dual Boost chopper NPT IGBT Power Module

14

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$V_{CES} = 1200V$ $I_{C} = 50A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction (PFC)
- Interleaved PFC

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS compliant

Absolute maximum ratings

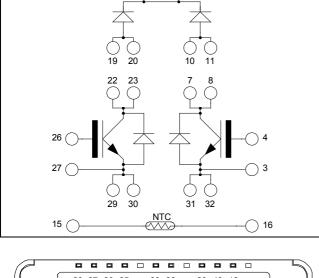
Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	70	
I _C	Continuous Collector Current	$T_c = 80^{\circ}C$	50	А
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	100A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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www.microsemi.com





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
ICES	Zero Gate Voltage Collector Current	$V_{CE} = 1200V$	$T_{i} = 125^{\circ}C$			500	μΛ
N/	Callester Engitter extension Valtere	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
V _{CE(sat)}	Collector Emitter saturation Voltage	$I_C = 50A$	$T_{j} = 125^{\circ}C$		4.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$		4.5		6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20 V, V_{CE} = 0V$				100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			3450		
Coes	Output Capacitance	$V_{CE} = 25V$ f = 1MHz			330		pF
C _{res}	Reverse Transfer Capacitance				220		
Qg	Total gate Charge	$V_{GS} = 15V$			330		
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 600V$			35		nC
Q _{gc}	Gate – Collector Charge	$I_C = 50A$			200		
T _{d(on)}	Turn-on Delay Time	Inductive Switch		35			
Tr	Rise Time	$V_{GE} = 15V$			65		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 50A$ $R_G = 5 \Omega$			320		ns
$T_{\rm f}$	Fall Time				30		
T _{d(on)}	Turn-on Delay Time	Inductive Switch	hing (125°C)		35		ns
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$			65		
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 50$ A			360		
T _f	Fall Time	$R_G = 5 \Omega$	Ω		40		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		6.9		mJ
E _{off}	Turn-off Switching Energy	$I_C = 50A$ $R_G = 5 \Omega$	$T_j = 125^{\circ}C$		3.05		1113
I _{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus}$ $t_p \leq 10\mu s ; T_j = 1$			300		А

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	$V_{R} = 1200 V$	$T_j = 25^{\circ}C$			100	μA
1 KM		т _к 1200 т _ј	$T_{j} = 125^{\circ}C$			500	μπ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		60		Α
		$I_F = 60A$	= 60A			3	
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 120 {\rm A}$			3		V
		$I_F = 60A$	$T_{j} = 125^{\circ}C$		1.8		
t	Reverse Recovery Time		$T_j = 25^{\circ}C$		265		ns
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 60 \text{A}$ $V_{\rm R} = 800 \text{V}$	$T_j = 125^{\circ}C$	350	350		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 A/\mu s$	$T_j = 25^{\circ}C$		560		nC
	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		2890		IIC

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Thermal and package characteristics

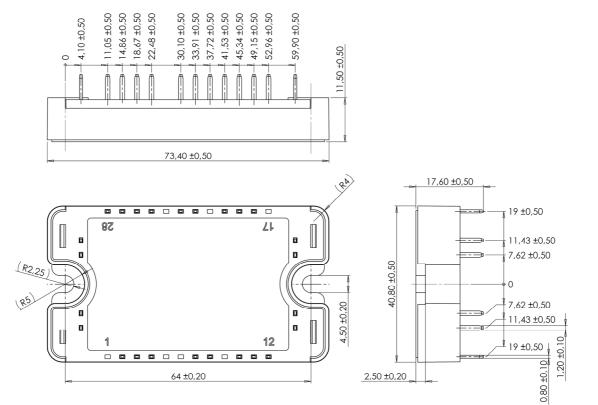
Symbol	Characteristic			Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IC	ЪΤ			0.4	°C/W	
R _{th} JC	Chop		Choppe	er diode			0.9	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz				4000			V
TJ	Operating junction temperature range				-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C	
T _C	Operating Case Temperature				-40		100	
Torque	Mounting torque	To heatsi	nk	M4	2		3	N.m
Wt	Package Weight						110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic			Тур	Max	Unit
R ₂₅	Resistance @ 25°C	5°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

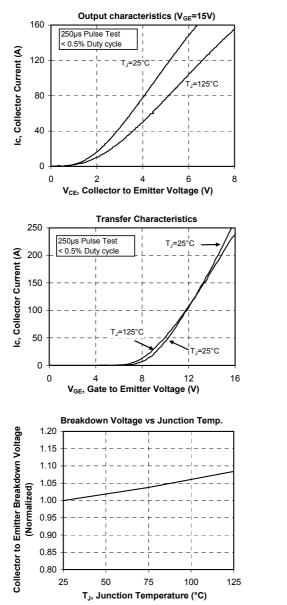


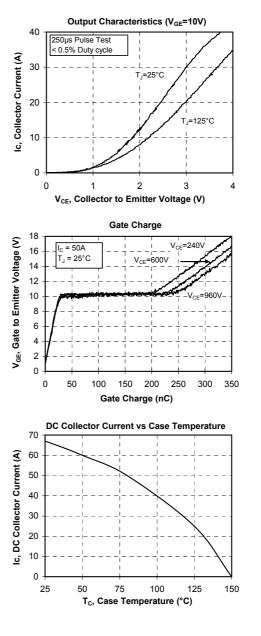
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

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Typical IGBT Performance Curve



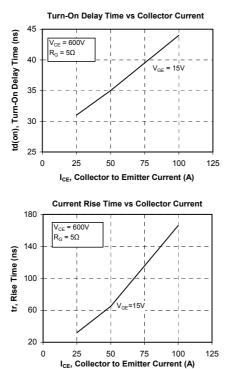


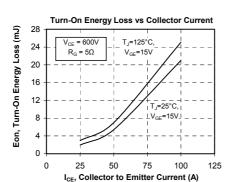
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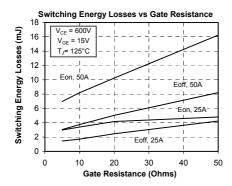
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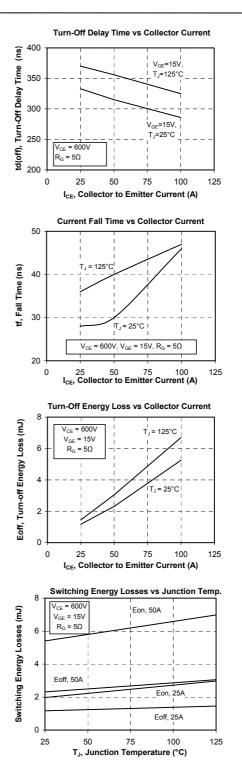
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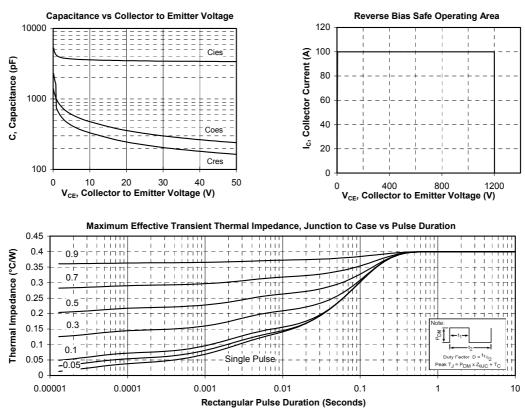




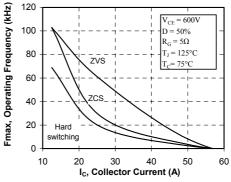


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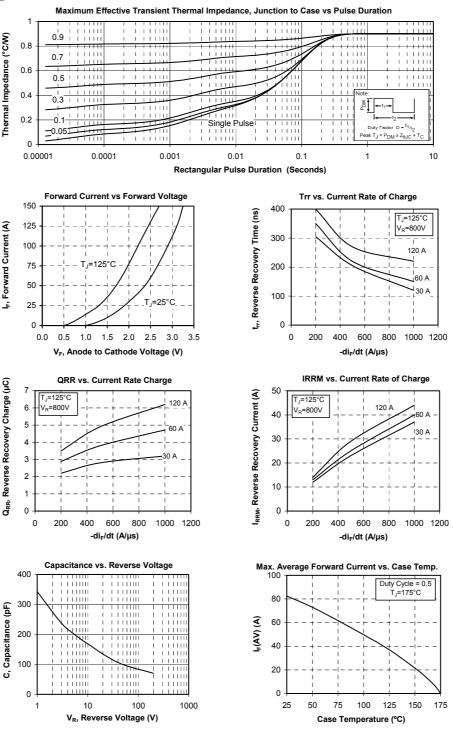
Operating Frequency vs Collector Current



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Typical chopper diode Performance Curve





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